

SG215

The SG215 photo interrupter high-performance standard type, combines high-output GaAs IRED with high sensitive phototransistor.

Features

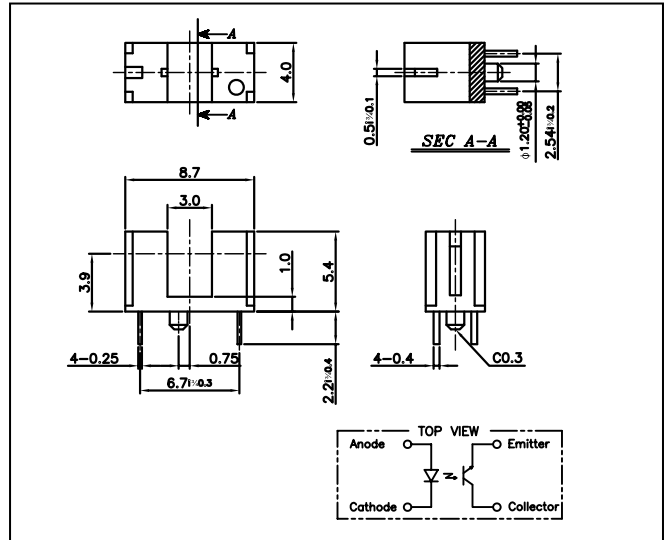
- PWB direct mount type
- High performance
- High speed response
- 3.0mm gap
- Widely applicable

Applications

- VTR
- Cassette mecha
- Printers
- Copiers

Dimensions

(Unit : mm)



Absolute Maximum Ratings

[Ta = 25°C]

Description		Symbol	Ratings	Unit
Input	Power dissipation	P_D	75	mW
	Forward current	I_F	50	mA
	Reverse voltage	V_R	5	V
	Pulse forward current *1	I_{FP}	-	A
Output	Collector power dissipation	P_C	75	mW
	Collector current	I_C	20	mA
	Collector-Emitter voltage	V_{CEO}	30	V
	Emitter-Collector voltage	V_{ECO}	5	V
Operating temp.		Topr.	-20~+75	°C
Storage temp.		Tstg.	-40~+75	°C
Soldering temp. *2		Tsol.	270	°C

*1. Input current with 10 μ s, T=10ms.

*2. Distance from end of the package = 2.0mm, time=5sec, MAX.

Electro-Optical Characteristics

[Ta = 25°C]

Parameter		Symbol	Conditions	Min.	Typ.	Max.	Unit.
Input	Forward voltage	V_F	$I_F=30mA$	-	1.2	1.5	V
	Reverse current	I_R	$V_R=5V$	-	-	10	μA
	Peak wavelength	λ_p		-	940	-	nm
Output	Collector dark current	I_{CEO}	$V_{CE}=10V, 0 I_x$	-	-	0.1	μA
Transmission	Collector current	I_C	$V_{CE}=5V, I_F=20mA$ (Non-Shading)	0.7	-	14	mA
	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_F=20mA, I_C=0.1mA$	-	-	0.4	V
Response Time	Rise time	t_r	$V_{CC}=10V, I_C=0.5mA$	-	10	-	μs
	Fall time	t_f	$R_L=100\Omega$	-	15	-	μs